Silicon NPN Power Transistors 2SD1243

DESCRIPTION

- With TO-3PN package
- Wide area of safe operation

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

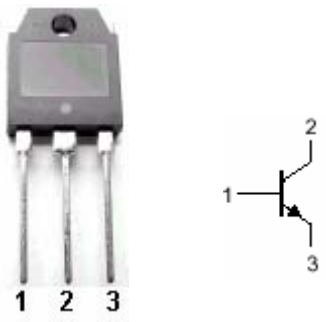


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	60	V
V_{CEO}	Collector-emitter voltage	Open base	60	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		10	A
I_{CM}	Collector current-peak		15	A
P_C	Collector power dissipation	T_C=25℃	100	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA ;I_B=0	60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=1mA ;I_E=0	60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5A ;I_B=0.5A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=5A ;I_B=0.5A			2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=60V; I_E=0			50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			50	μA
h_{FE}	DC current gain	I_C=3A ; V_{CE}=3V	50			

PACKAGE OUTLINE

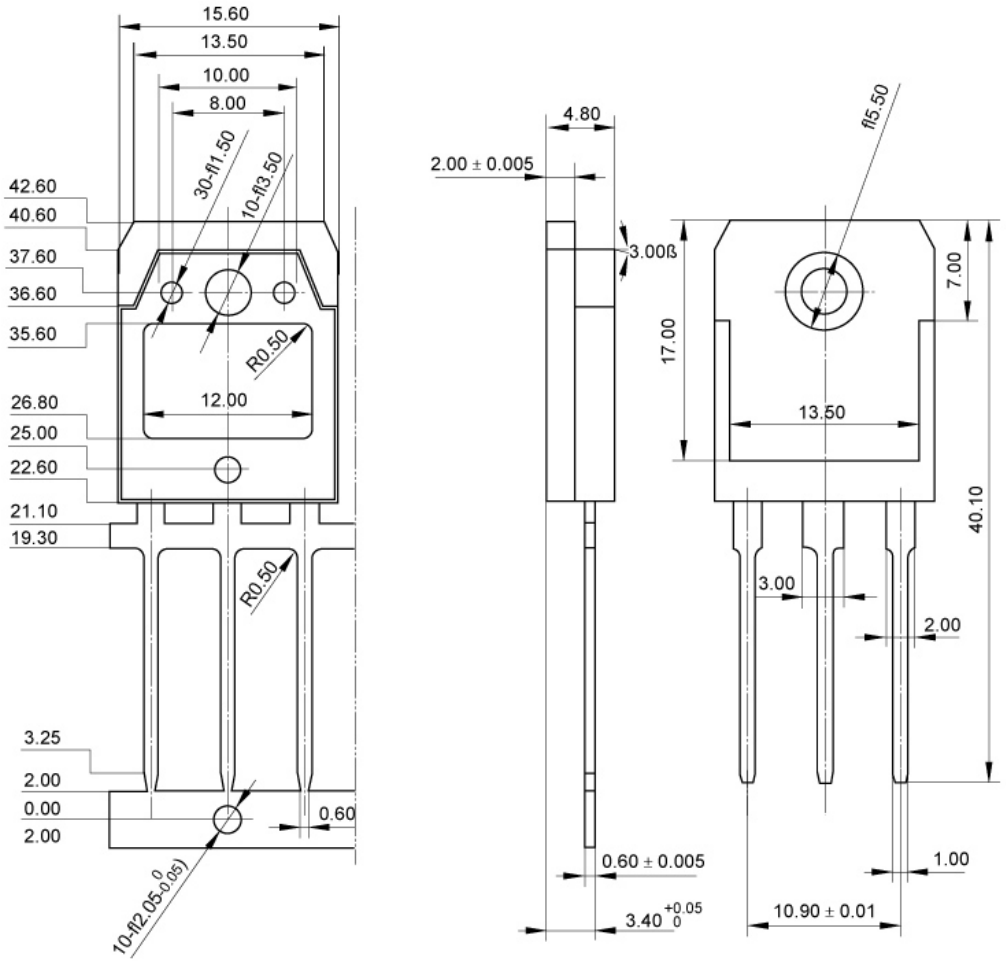


Fig.2 outline dimensions